# XP161A1265PR-G

ETR11023-004

#### **Power MOSFET**

# ■GENERAL DESCRIPTION

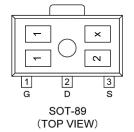
The XP161A1265PR is an N-channel Power MOSFET with low on-state resistance and ultra high-speed switching characteristics. Because high-speed switching is possible, the IC can be efficiently set thereby saving energy. A gate protect diode is built-in to prevent static damage.

The small SOT-89 package makes high density mounting possible.

### ■ APPLICATIONS

- Notebook PCs
- Cellular and portable phones
- On-board power supplies
- Li-ion battery systems

#### ■ PIN CONFIGURATION/ MARKING



G : Gate S : Source

D : Drain

### ■FEATURES

Low On-State Resistance : Rds(on)=0.055 Ω@ Vgs=4.5V : Rds(on)=0.095 Ω@ Vgs=2.5V Ultra High-Speed Switching Gate Protect Diode Built-in Driving Voltage : 2.5V N-Channel Power MOSFET DMOS Structure Package : SOT-89

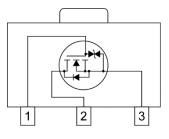
#### ■PRODUCT NAME

PRODUCT	PACKAGE	ORDER UNIT
XP161A1265PR-G*	SOT-89	1,000pcs/Reel

(\*) The "-G" suffix denotes Halogen and Antimony free as well as being fully RoHS compliant

\* x represents production lot number.

# ■EQUIVALENT CIRCUIT



N-channel MOSFET (1 device built-in)

# ■ABSOLUTE MAXIMUM RATINGS

		Ta	<u>= 25°C</u>
PARAMETER	SYMBOL	RATINGS	UNITS
Drain-Source Voltage	Vdss	20	V
Gate-Source Voltage	Vgss	±12	V
Drain Current (DC)	ld	4	А
Drain Current (Pulse)	ldp	16	А
Reverse Drain Current	ldr	4	А
Channel Power Dissipation *	Pd	2	W
Channel Temperature	Tch	150	°C
Storage Temperature Range	Tstg	-55~150	°C

\* When implemented on a ceramic PCB (900mm<sup>2</sup> x 0.8mm)

# XP161A1265PR-G

# ■ ELECTRICAL CHARACTERISTICS

#### DC Characteristics

Ta = 25°C

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PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Drain Cut-Off Current	ldss	Vds=20V, Vgs= 0V	-	-	10	μA
Gate-Source Leak Current	lgss	Vgs= $\pm$ 12V, Vds= 0V	-	-	±10	μA
Gate-Source Cut-Off Voltage	Vgs(off)	ld= 1mA, Vds= 10V	0.7	-	1.4	V
Drain-Source On-State Resistance*1	Rds(on)	ld= 2A, Vgs= 4.5V	-	0.042	0.055	Ω
		ld= 2A, Vgs= 2.5V	-	0.070	0.095	Ω
Forward Transfer Admittance*1	Yfs	ld= 2A, Vds= 10V	-	8	-	S
Body Drain Diode Forward Voltage	Vf	lf= 4A, Vgs= 0V	-	0.85	1.1	V

\*1 Effective during pulse test.

#### **Dynamic Characteristics**

Dy	namic Characteristics					Та	= 25°C
	PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
	Input Capacitance	Ciss		-	320	-	pF
	Output Capacitance	Coss	Vds= 10V, Vgs=0V f= 1MHz	-	190	-	pF
	Feedback Capacitance	Crss	1 111112	-	80	-	pF

#### **Switching Characteristics**

Ta = 2	25°C
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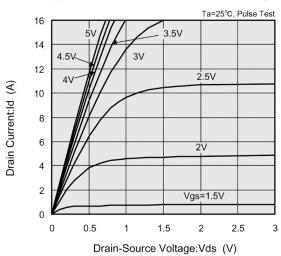
PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Turn-On Delay Time	td (on)		-	10	-	ns
Rise Time	tr	Vgs= 5V, Id=2A	-	15	-	ns
Turn-Off Delay Time	td (off)	Vdd= 10V	-	55	-	ns
Fall Time	tf		-	40	-	ns

#### **Thermal Characteristics**

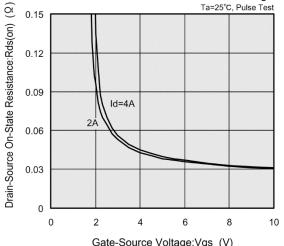
PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal Resistance (Channel-Ambience)	Rth (ch-a)	Implement on a ceramic PCB	-	62.5	-	°C/W

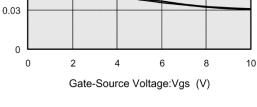
## ■TYPICAL PERFORMANCE CHARACTERISTICS

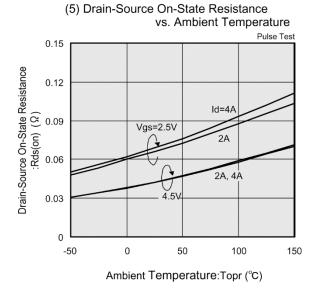
(1) Drain Current vs. Drain-Source Voltage

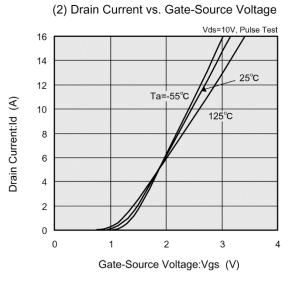


(3) Drain-Source On-State Resistance vs. Gate-Source Voltage

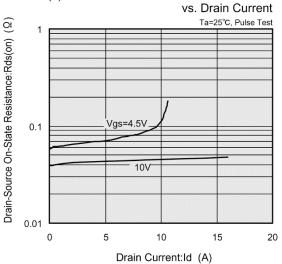


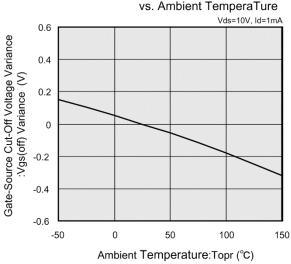






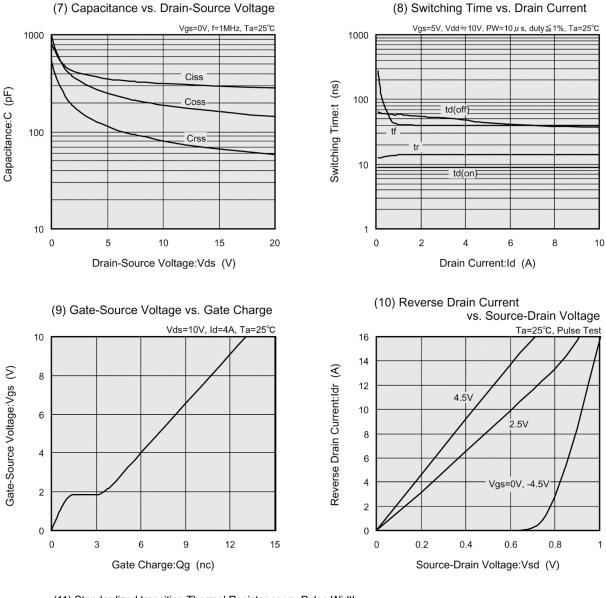
(4) Drain-Source On-State Resistance

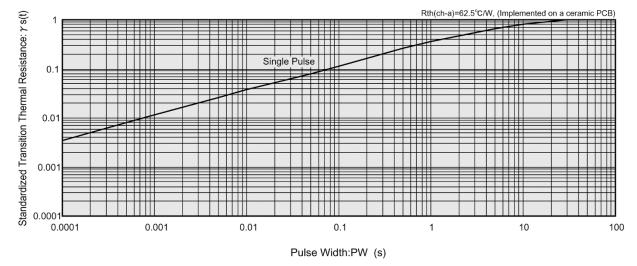




(6) Gate-Source Cut-Off Voltage Variance vs. Ambient TemperaTure

# ■TYPICAL PERFORMANCE CHARACTERISTICS (Continued)





(11) Standardized transition Thermal Resistance vs. Pulse Width

# ■PACKAGING INFORMATION

For the latest package information go to, <u>www.torexsemi.com/technical-support/packages</u>

PACKAGE	OUTLINE / LAND PATTERN	THERMAL CHARACTERISTICS
SOT-89	<u>SOT-89 PKG</u>	SOT-89 Power Dissipation

# XP161A1265PR-G

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